

6. (Original) A side-emission type semiconductor light-emitting device according to claim 5, wherein said one main surface is a surface brought into contact with said transparent or translucent resin, and said other main surface is a surface exposed to outside.

7. (Currently Amended) A side-emission type semiconductor light-emitting device according to ~~any one of claims 4 to 6~~ claim 4, wherein said LED chip has a bonding wire extending from a top surface, and said concave portion is formed directly above said LED chip.

8. (Original) A manufacturing method of a side-emission type semiconductor light-emitting device, comprising the following steps of:

- (a) mounting a reflector formed with a concave portion on a substrate;
- (b) removing an organic matter adhering to a surface, including an inner surface of said concave portion, of said reflector; and
- (c) injecting a transparent or translucent resin between said reflector and said substrate up to said concave portion.

9. (Original) A manufacturing method of a side-emission type semiconductor light-emitting device according to claim 8, wherein said reflector is subjected to UV cleaning in the step (b).

10. (Cancelled)

11. (Cancelled)

12. (Cancelled)

13. (Cancelled)

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14. (New) A side-emission type semiconductor light-emitting device according to claim 5, wherein said LED chip has a bonding wire extending from a top surface, and said concave portion is formed directly above said LED chip.

15. (New) A side-emission type semiconductor light-emitting device according to claim 6, wherein said LED chip has a bonding wire extending from a top surface, and said concave portion is formed directly above said LED chip.